

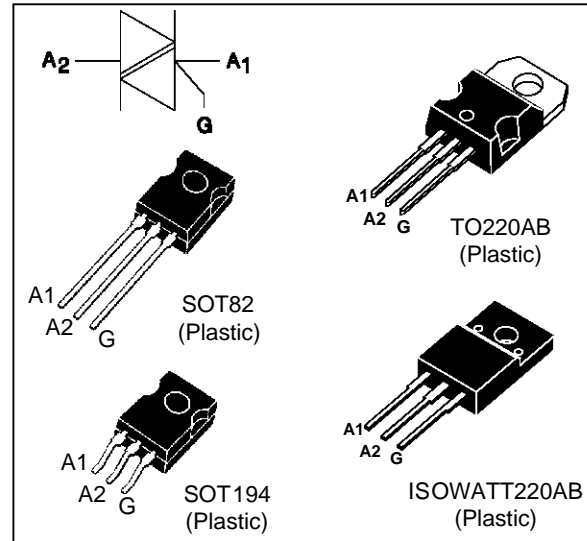
HIGH PERFORMANCE TRIACS

FEATURES

- $I_{TRMS} = 4\text{ A}$
- $V_{DRM} = 400\text{ V to }600\text{ V}$
- SENSITIVE GATE : $I_{GT} \leq 5\text{ mA}$
- LOW $I_H \leq 10\text{ mA}$

DESCRIPTION

The T405 high voltage TRIAC Families are high performance planar diffused PNP devices glass passivated technology. Packaged either in TO220AB, SOT82, SOT194 and ISOWATT220AB these products are intended for all bidirectional switch applications.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit	
$I_T(\text{RMS})$	RMS on-state current (360° conduction angle)	TO220AB SOT194/SOT82	$T_c = 95\text{ °C}$	4	A
		ISOWATT220AB	$T_c = 85\text{ °C}$		
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = 25°C)		$t_p = 8.3\text{ ms}$	35	A
			$t_p = 10\text{ ms}$		
i^2t	i^2t value		$t_p = 10\text{ ms}$	4.5	A ² s
di/dt	Critical rate of rise of on-state current Gate supply : $I_G = 50\text{ mA}$ $di_G/dt = 1\text{ A}/\mu\text{s}$		Repetitive $F = 50\text{ Hz}$	10	A/ μs
			Non Repetitive	50	
T_{stg} T_j	Storage and operating junction temperature range		- 40 to + 150 - 40 to + 110		°C °C
T_l	Maximum lead temperature for soldering during 10 s at 4.5 mm from case		260		°C

Symbol	Parameter	T405		Unit
		-400	-600	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage $T_j = 110\text{ °C}$	400	600	V

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
Rth (j-a)	Junction to ambient	SOT82 / SOT194	100	°C/W
		TO220AB	60	
		ISOWATT220AB	50	
Rth (j-c) DC	Junction to case for DC	SOT82 / SOT194 TO220AB	3.5	°C/W
		ISOWATT220AB	5.3	
Rth (j-c) AC	Junction to case for 360° conduction angle (F= 50 Hz)	SOT82 / SOT194 TO220AB	2.6	°C/W
		ISOWATT220AB	4	

GATE CHARACTERISTICS (maximum values)

$P_{G(AV)} = 1 \text{ W}$ $P_{GM} = 40 \text{ W}$ (tp = 20 μs) $I_{GM} = 4 \text{ A}$ (tp = 20 μs) $V_{GM} = 16 \text{ V}$ (tp = 20 μs).

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions		Quadrant		Value	Unit
I_{GT}	$V_D=12\text{V}$ (DC) $R_L=33\Omega$	$T_j=25^\circ\text{C}$	I-II-III	MAX	5	mA
V_{GT}	$V_D=12\text{V}$ (DC) $R_L=33\Omega$	$T_j=25^\circ\text{C}$	I-II-III	MAX	1.5	V
V_{GD}	$V_D=V_{DRM}$ $R_L=3.3\text{k}\Omega$	$T_j=110^\circ\text{C}$	I-II-III	MIN	0.2	V
tgt	$V_D=V_{DRM}$ $I_G = 40\text{mA}$ $di_G/dt = 0.5\text{A}/\mu\text{s}$ $I_{TM} = 5.5\text{A}$	$T_j=25^\circ\text{C}$	I-II-III	TYP	2	μs
I_L	$I_G=1.2 I_{GT}$	$T_j=25^\circ\text{C}$	I-III	MAX	10	mA
			II	max	15	
I_H *	$I_T=100\text{mA}$ gate open	$T_j=25^\circ\text{C}$		MAX	10	mA
V_{TM} *	$I_{TM}=5.5\text{A}$ tp= 380 μs	$T_j=25^\circ\text{C}$		MAX	1.75	V
I_{DRM} I_{RRM}	V _{DRM} Rated V _{RRM} Rated	$T_j=25^\circ\text{C}$		MAX	0.01	mA
		$T_j=110^\circ\text{C}$		MAX	2	
dV/dt *	Linear slope up to $V_D=67\%V_{DRM}$ gate open	$T_j=110^\circ\text{C}$		MIN	5	V/ μs
				TYP	20	
(di/dt) _c *	(dV/dt) _c = 0.1V/ μs	$T_j=110^\circ\text{C}$		MIN	1.8	A/ms

* For either polarity of electrode A₂ voltage with reference enceenceto electrode A₁.

ORDERING INFORMATION

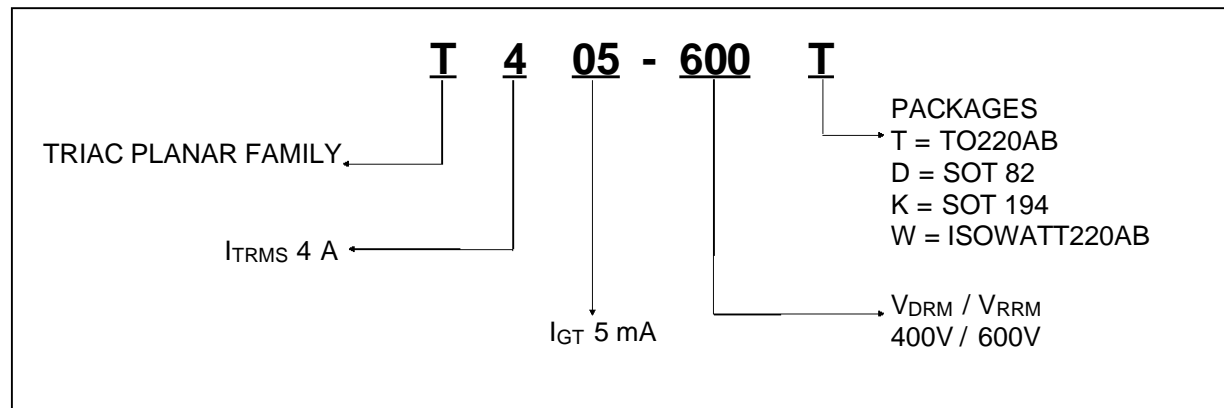


Fig.1 : Maximum power dissipation versus RMS on-state current (F=50Hz).
(Curves are cut off by (di/dt)c limitation)

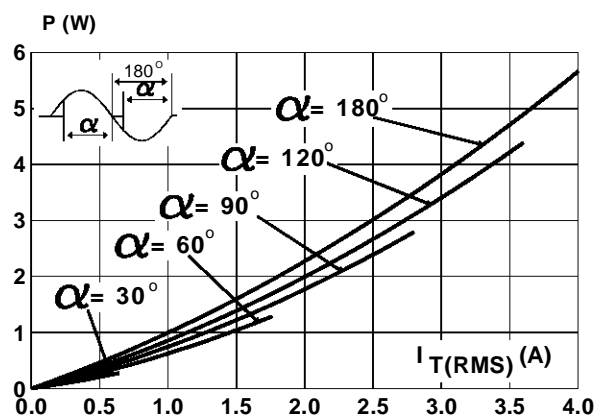


Fig.3 : Correlation between maximum RMS power dissipation and maximum allowable temperatures (Tamb and Tcase) for different thermal resistances heatsink + contact (ISOWATT220AB).

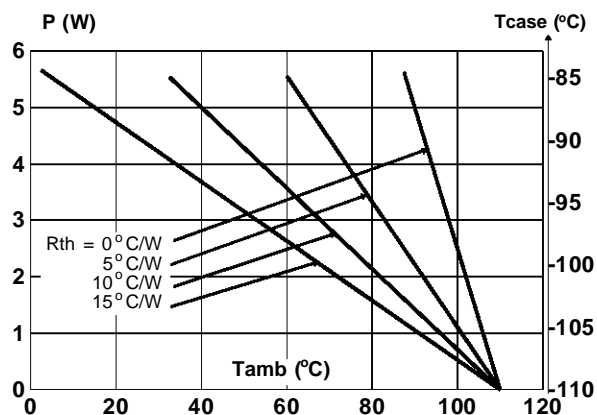


Fig.2 : Correlation between maximum power dissipation and maximum allowable temperatures (Tamb and Tcase) for different thermal resistances heatsink + contact (TO220AB / SOT82 / SOT194).

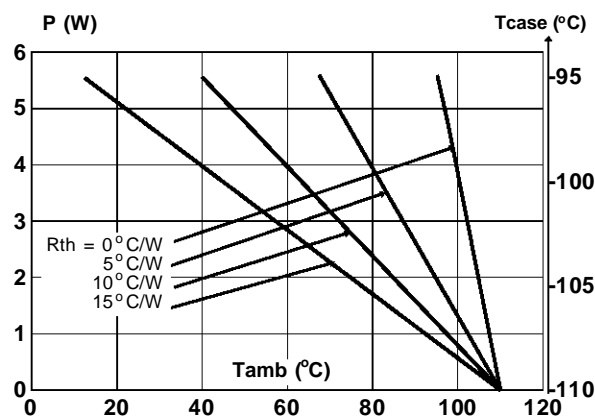


Fig.4 : RMS on-state current versus case temperature.

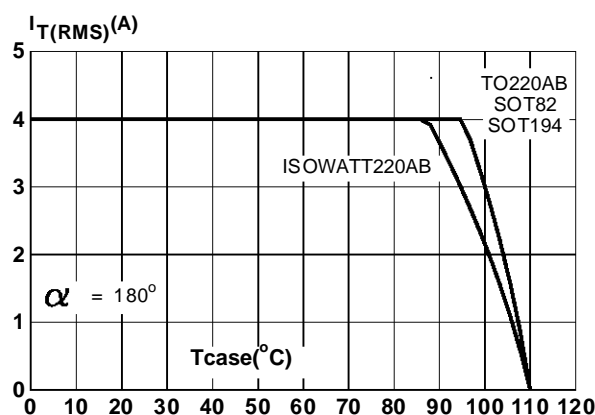


Fig.5 : Relative variation of thermal impedance versus pulse duration (SOT82 / SOT194 / TO220AB only).

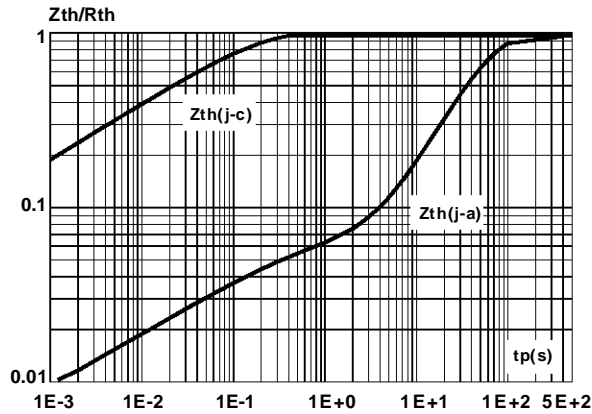


Fig.6 : Relative variation of thermal impedance versus pulse duration (ISOWATT220AB only).

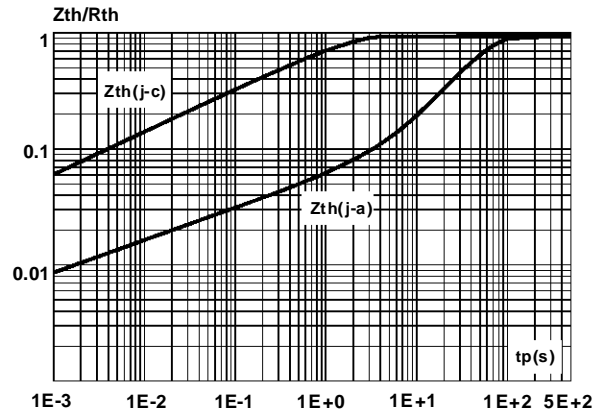


Fig.7 : Relative variation of gate trigger current and holding current versus junction temperature.

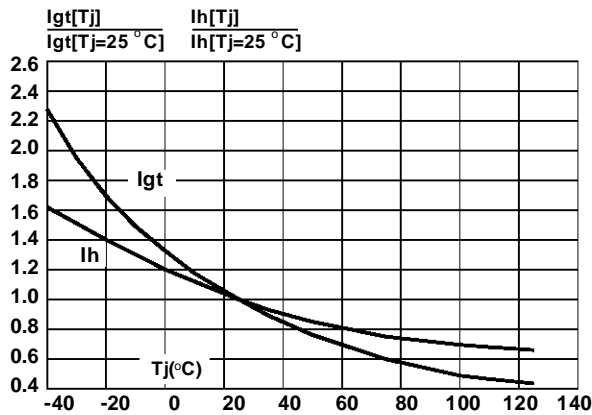


Fig.8 : Non Repetitive surge peak on-state current versus number of cycles.

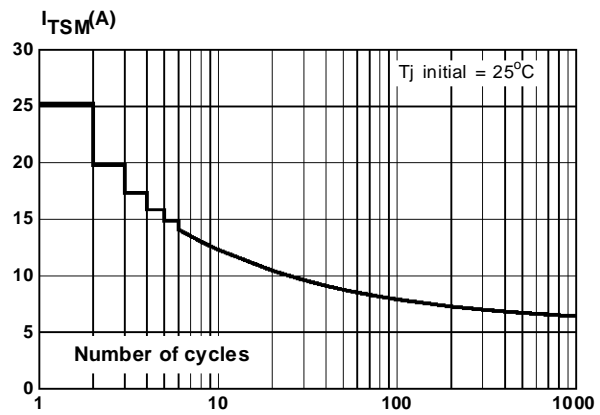


Fig.9 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : $tp \leq 10ms$, and corresponding value of I^2t .

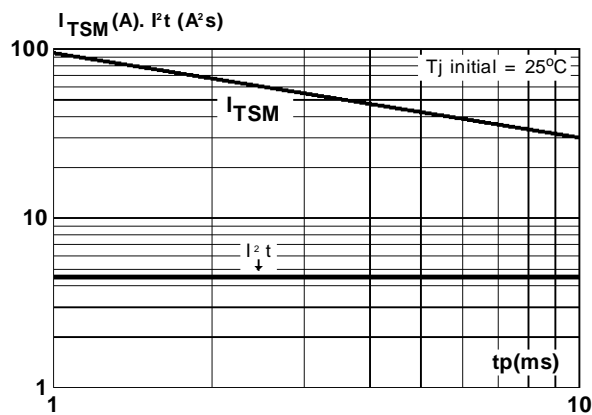
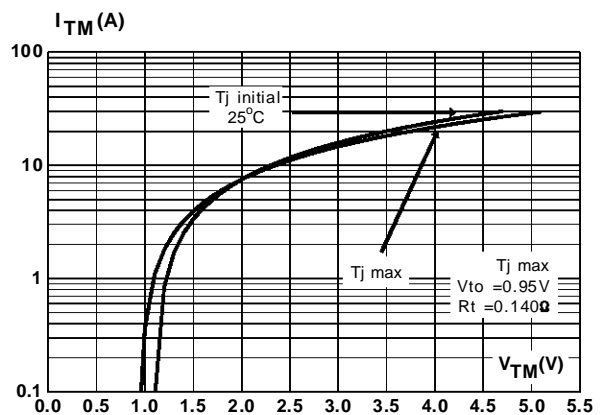
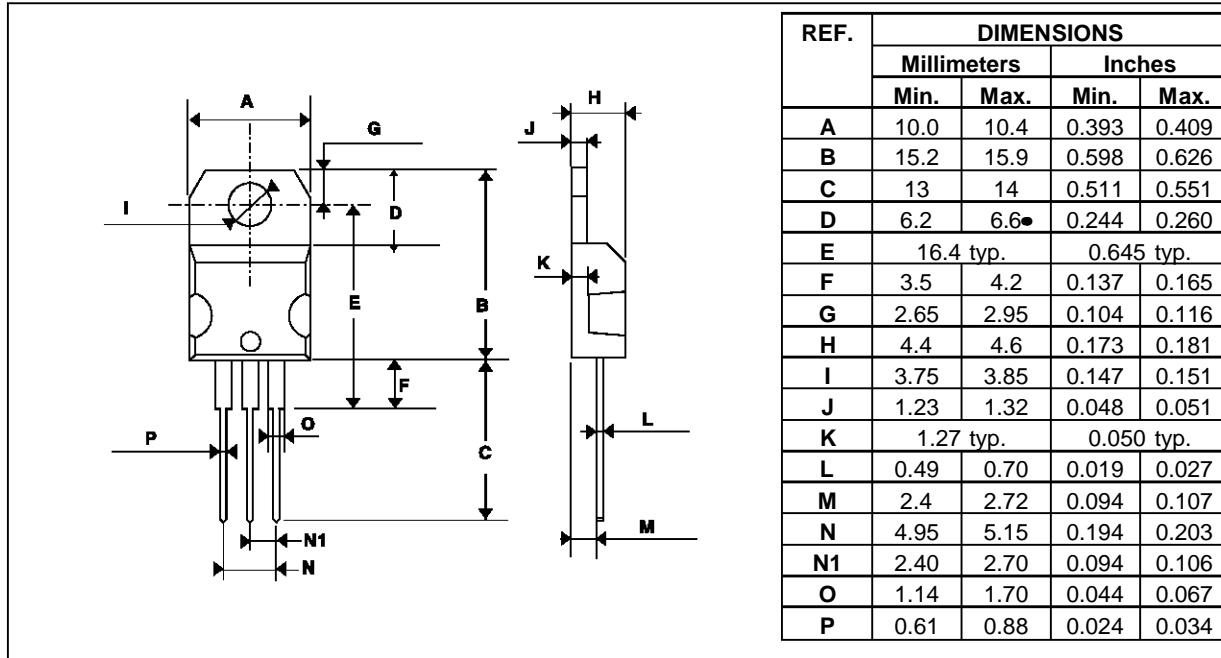


Fig.10 : On-state characteristics (maximum values).

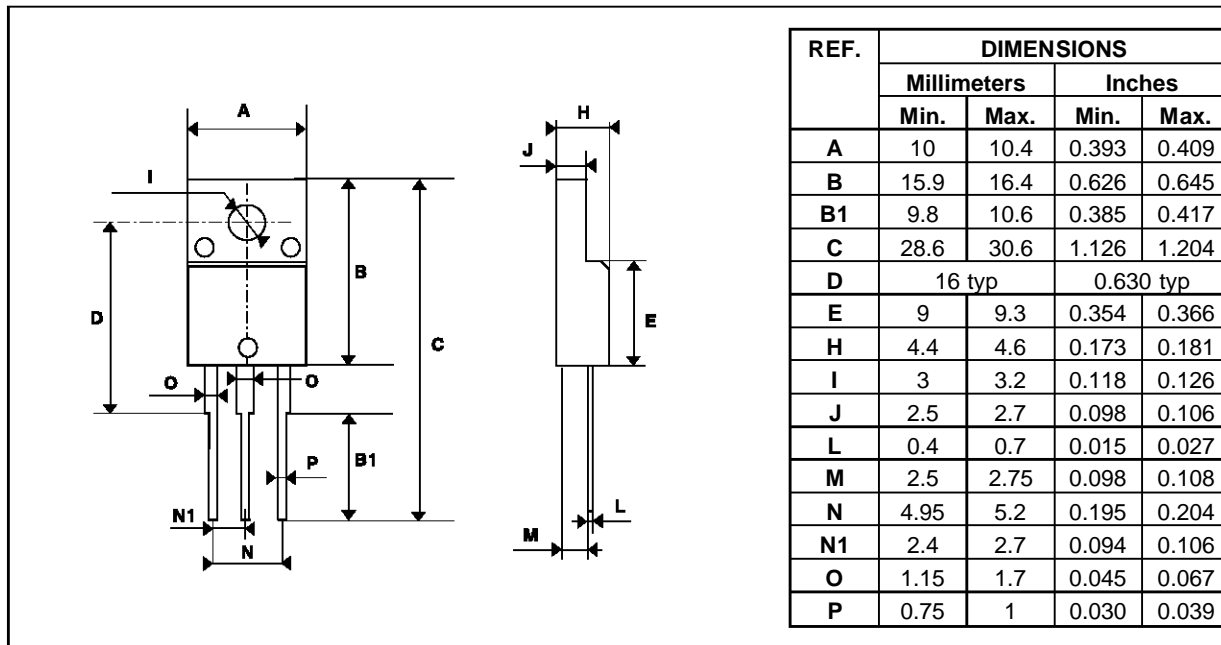


PACKAGE MECHANICAL DATA
TO220AB Plastic



Cooling Method : C
 Marking : Type number
 Weight : 2 g
 Recommended torque value : 0.55 m.N.
 Maximum torque value : 0.70 m.N.

PACKAGE MECHANICAL DATA
ISOWATT220AB Plastic

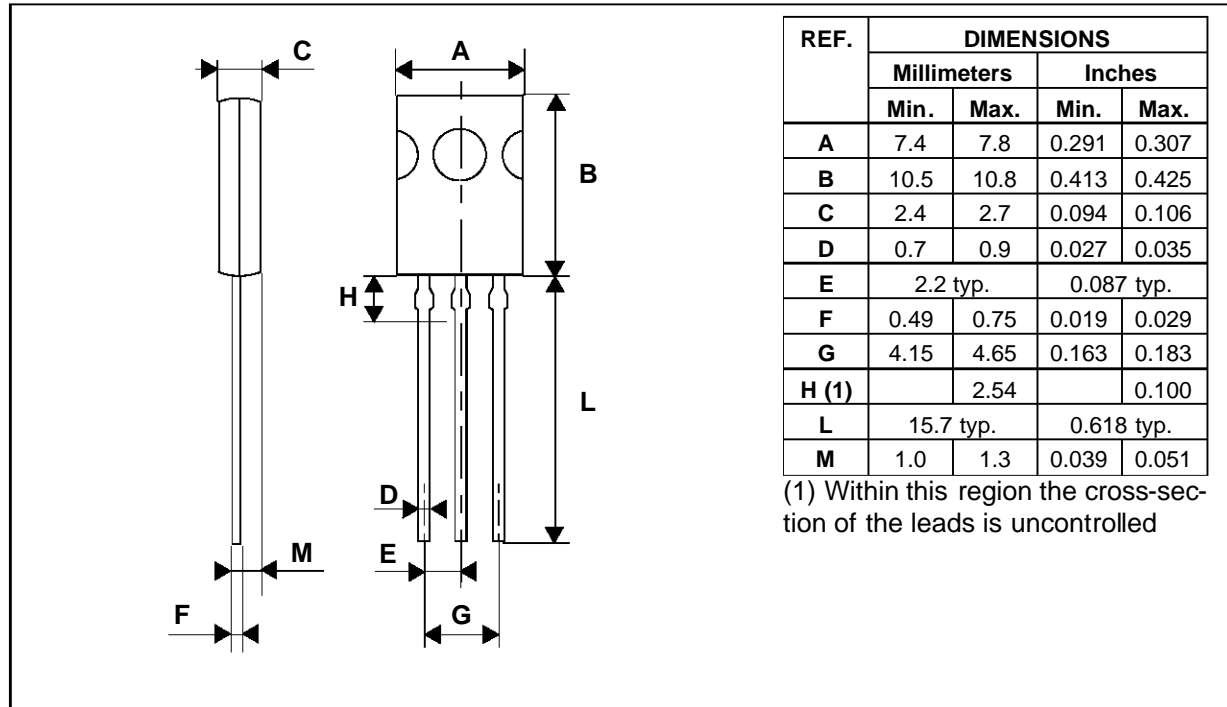


Cooling Method : C
 Marking : Type number
 Weight : 2.1g
 Recommended torque value : 0.55 m.N.
 Maximum torque value : 0.70 m.N.

T405

PACKAGE MECHANICAL DATA

SOT 82 Plastic

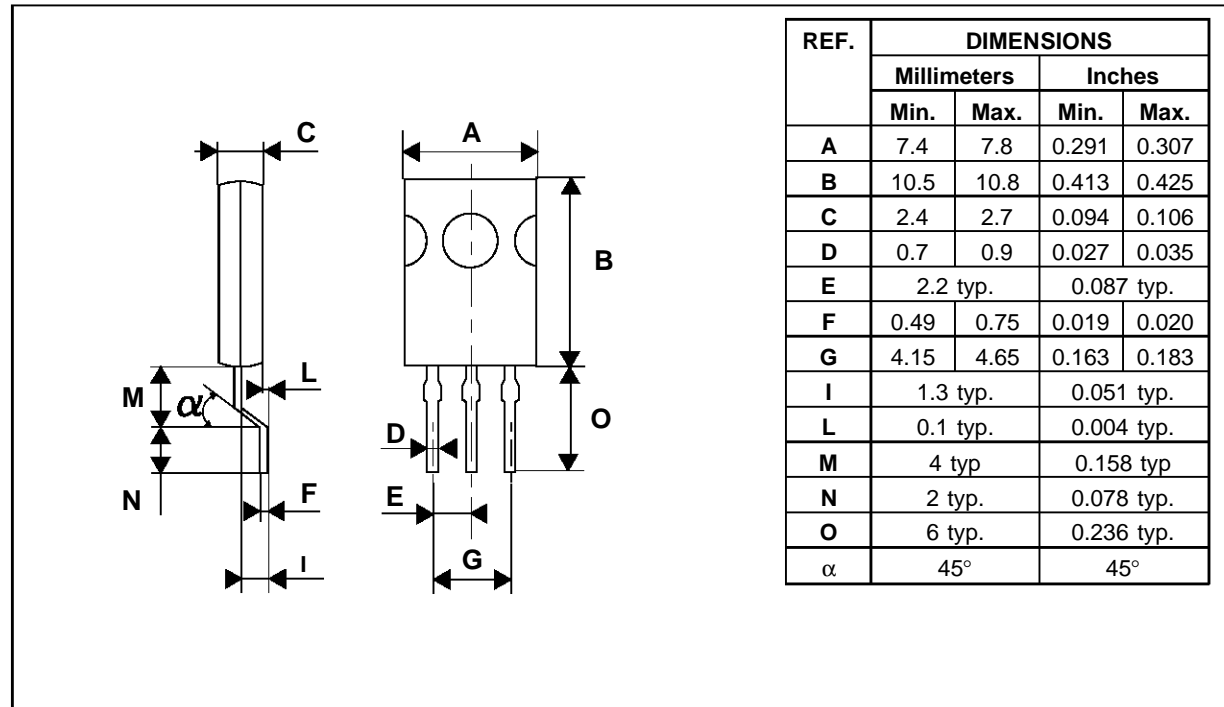


Marking : Type number

Weight : 0.72g

PACKAGE MECHANICAL DATA

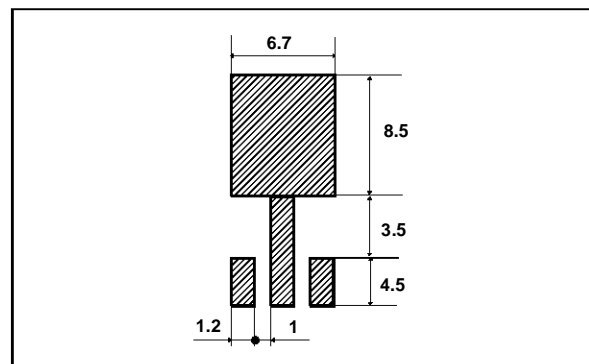
SOT 194 Plastic



Marking : Type number

Weight : 0.68g

FOOT PRINT



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